

SEL533-03

Infrared Emitting Diodes(GaAs)

The SEL533-03 is a GaAs infrared emitting diode mounted in $\Phi 3\text{mm}$ all plastic mold package. It is both compact and easy to mount.

Features

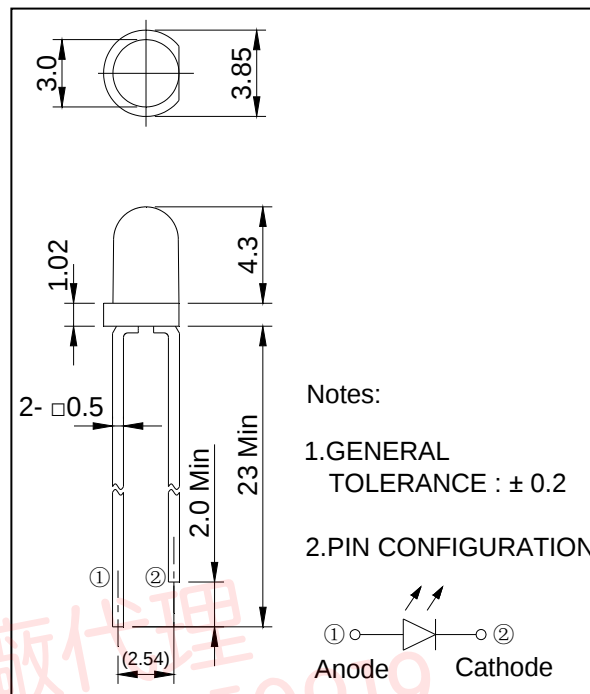
- Small size
- High power
- High reliability
- Compact ($\Phi 3\text{mm}$)

Application

- Smoke sensor
- Financial equipment
- Optical switches

Dimensions

(Unit:mm)



MAXIMUM RATINGS

(Ta= 25°C)

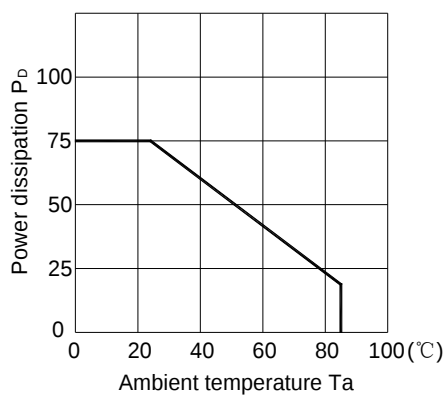
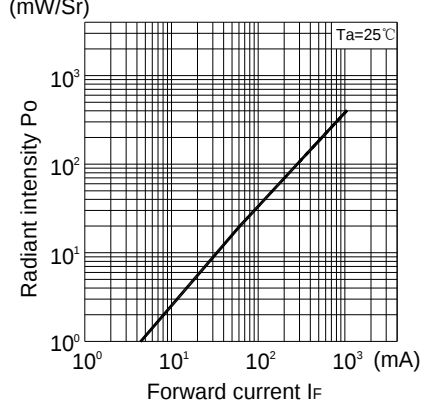
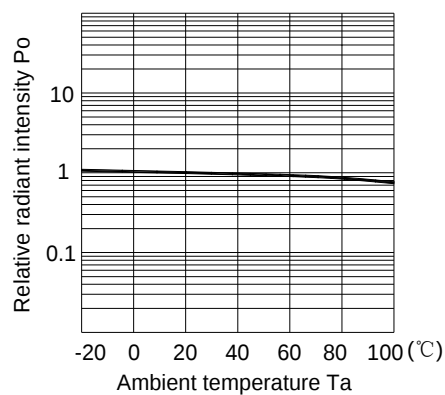
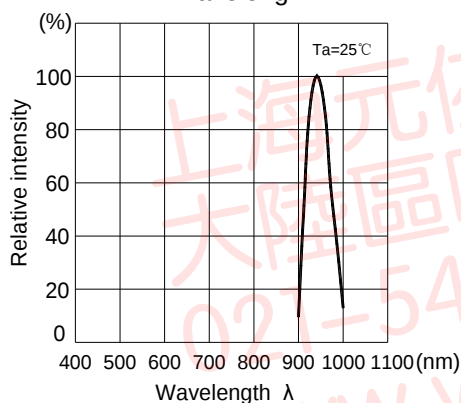
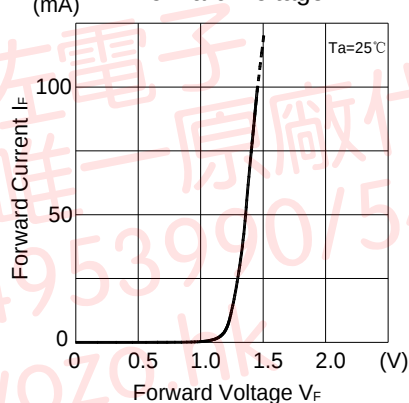
Item	Symbol	Rating	Unit
Power dissipation	P _D	75	mW
Forward current	I _F	50	mA
Reverse voltage	V _R	5	V
Operating temp.	T _{opr.}	-25~+85	°C
Storage temp.	T _{stg.}	-30~+100	°C
Soldering temp. ^{*1}	T _{sol.}	260	°C

*1. Lead Soldering Temperature(3mm from case for 5sec)

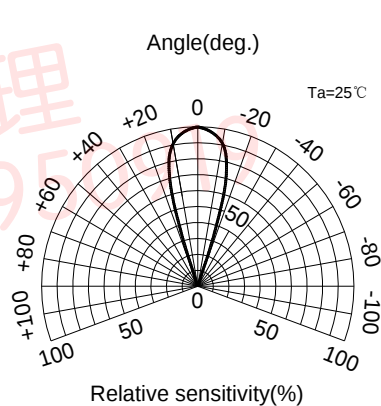
ELECTRO- OPTICAL CHARACTERISTICS

(Ta= 25°C)

Items	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage	V _F	I _F =50mA	-	1.4	1.6	V
Reverse current	I _R	V _R =5V	-	-	10	μA
Radiant intensity	I _E	I _F =20mA	-	6	-	mW
Peak wavelength	λ _p	I _F =20mA	-	940	-	nm
Spectral bandwidth	Δλ	I _F =20mA	-	45	-	nm
Half angle	Δθ	I _F =20mA	-	±18	-	deg.

Power dissipation Vs.
Ambient temperatureRadiant intensity Vs.
Forward currentRelative radiant intensity Vs.
Ambient temperatureRelative intensity Vs.
WavelengthForward current Vs.
Forward Voltage

Radiant Pattern

Relative radiant intensity Vs.
Distance